KUU SEMICONDUCTOR

KPESD5V0C1BL

TVS/ESD Protection Diode

DESCRIPTION

KPESD5V0C1BL is a low-capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for data, control or power lines. With typical capacitance of 10pF only, is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 (±15kV air, ±8kV contact discharge), IEC 61000-4-4 (electrical fast transient - EFT) (40A, 5/50 ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

The KPESD5V0C1BL uses ultra-small DFN1006 package. Each device can protect one data line. It offers system designers flexibility to protect single data line where space is a premium concern.

FEATURES

- ✧Transient protection for high-speed data lines
  - IEC 61000-4-2 (ESD) ±15kV (Air)
  - ±8kV (Contact)
  - IEC 61000-4-4 (EFT) 40A (5/50 ns)
  - Cable Discharge Event (CDE)
- ✧Package optimized for high-speed lines
- ✧Ultra-small package (1.0mm×0.6mm×0.4mm)
- ✧Protects one data, control or power line
- ✧Low capacitance
- ✧Low leakage current
- ✧Low clamping voltage
- ✧Each I/O pin can withstand over 1000 ESD strikes for ±8kV contact discharge

MACHANICAL DATA

- ✧DFN1006 package
- ✧Flammability Rating: UL 94V-0
- ✧Packaging: Tape and Reel
- ✧High temperature soldering guaranted:260℃/10s
- ✧Reel size: 7 inch
- ✧MSL3

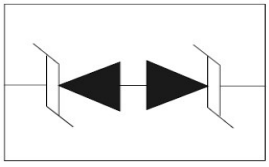
ORDERING INFORMATION

- ✧Package: DFN1006
- ✧Marking: FOC
- ✧Material: RoHS compliant, Halogen free
- ✧Packing: Tape & Reel
- ✧Quantity per reel: 10,000pcs

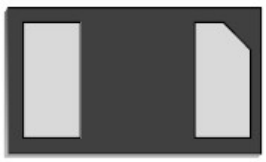
APPLICATIONS

- ✧Portable Electronics
- ✧Desktops, Servers and Notebooks
- ✧Cellular Phones
- ✧MP3 Ports
- ✧Digital Ports
- ✧Subscriber Identity Module (SIM) card

CIRCUIT DIAGRAM



PIN CONFIGURATION



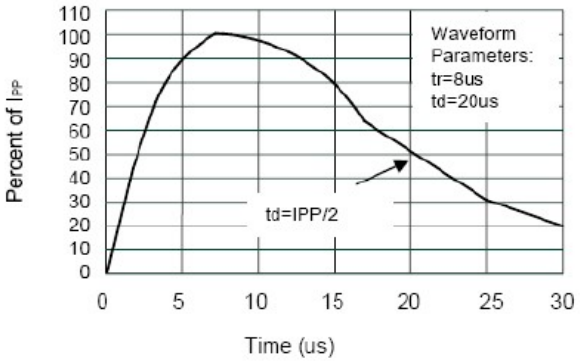
ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Units
V_{ESD}	ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	±30 ±30	kV
P_{PP}	Peak Pulse Power (8/20μs)	150	W
T_{OPT}	Operating Temperature	-40~150	°C
T_{STG}	Storage Temperature	-40~150	°C

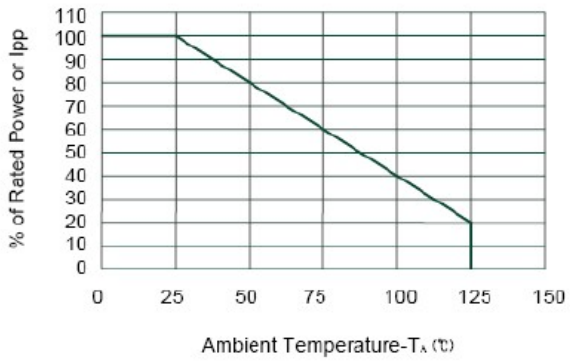
ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
V_{RWM}	Reverse Working Voltage				5.0	V
V_{BR}	Reverse Breakdown Voltage	I_T = 1mA	5.6		7.8	V
I_R	Reverse Leakage Current	V_{RWM} = 5V			1.0	μA
V_C	Clamping Voltage	I_{PP} = 5A, t_p = 8/20μs			11.6	V
V_C	Clamping Voltage	I_{PPmax} = 9.4A , t_p = 8/20μs			16.0	V
C_J	Junction Capacitance	V_R = 0V, f = 1MHz		10	15	pF

ELECTRICAL CHARACTERISTICS CURVE

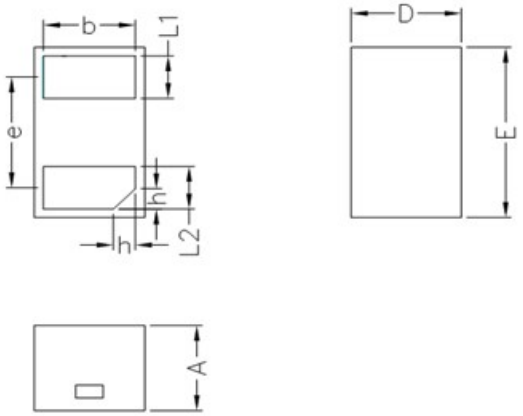


Pulse Waveform



Power Derating Curve

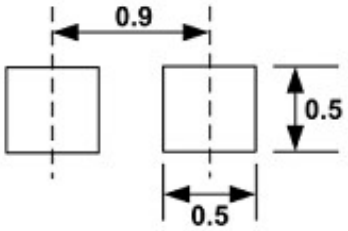
DFN1006 PACKAGE OUTLINE DIMENSIONS



Unit: mm

	MIN	NOM	MAX
D	0.55	0.60	0.65
E	0.95	1.00	1.05
L1	0.20	0.25	0.30
L2	0.20	0.25	0.30
b	0.45	0.50	0.55
e	0.65BSC		
A	0.45	0.50	0.55
h	0.07	0.12	0.17

Dimension: Millimeter
(Stencil thickness: 0.1)



Soldering Footprint